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ABSTRACT OF THE DISCLOSURE

Nickel is introduced to a predetermined region of a peripheral circuit section, other than a picture element section, on an amorphous silicon film to crystallize from that region. After forming gate electrodes and others, sources, drains and channels are formed by doping impurities, and laser is irradiated to improve the crystallization. After that, electrodes/wires are formed. Thereby an active matrix type liquid crystal display whose thin film transistors (TFT) in the peripheral circuit section are composed of the crystalline silicon film whose crystal is grown in the direction parallel to the flow of carriers and whose TFTs in the picture element section are composed of the amorphous silicon film can be obtained.